

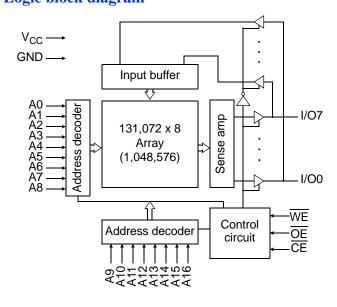
## 3.3V 128K X 8 CMOS SRAM (Center power and ground)

#### **Features**

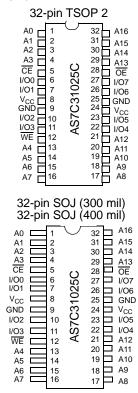
- Industrial and commercial temperatures
- Organization: 131,072 x 8 bits
- · High speed
- 10 ns address access time
- 5 ns output enable access time
- Low power consumption via ship deselect
- Easy memory expansion with  $\overline{CE}$ ,  $\overline{OE}$  inputs
- · Center power and ground
- TTL/LVTTL-compatible, three-state I/O
- JEDEC-standard packages

- 32-pin, 300 mil SOJ
- 32-pin, 400 mil SOJ
- 32-pin, TSOP 2
- ESD protection ≥ 2000 volts

# Logic block diagram



### Pin arrangement





### **Functional description**

The AS7C31025C is 3V a high-performance CMOS 1,048,576-bit Static Random Access Memory (SRAM) device organized as 131,072 x 8 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times  $(t_{AA}, t_{RC}, t_{WC})$  of 10 ns with output enable access times  $(t_{OE})$  of 5 ns are ideal for high-performance applications. The chip enable input  $\overline{CE}$  permits easy memory and expansion with multiple-bank memory systems.

When  $\overline{\text{CE}}$  is high the device enters standby mode. A write cycle is accomplished by asserting write enable ( $\overline{\text{WE}}$ ) and chip enable ( $\overline{\text{CE}}$ ). Data on the input pins I/O0 through I/O7 is written on the rising edge of  $\overline{\text{WE}}$  (write cycle 1) or  $\overline{\text{CE}}$  (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ( $\overline{\text{OE}}$ ) or write enable ( $\overline{\text{WE}}$ ).

A read cycle is accomplished by asserting output enable  $(\overline{OE})$  and chip enable  $(\overline{CE})$ , with write enable  $(\overline{WE})$  high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive or write enable is active, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and operation is from a single 3.3 V supply. The AS7C31025C is packaged in common industry standard packages.

### **Absolute maximum ratings**

Parameter	Symbol	Min	Max	Unit
Voltage on V <sub>CC</sub> relative to GND	$V_{t1}$	-0.50	+4.6	V
Voltage on any pin relative to GND	V <sub>t2</sub>	-0.50	$V_{CC} + 0.5$	V
Power dissipation	$P_{\mathrm{D}}$	_	1.25	W
Storage temperature (plastic)	T <sub>stg</sub>	-55	+125	° C
Ambient temperature with V <sub>CC</sub> applied	T <sub>bias</sub>	-55	+125	° C
DC current into outputs (low)	I <sub>OUT</sub>	_	50	mA

NOTE: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### Truth table

CE	WE	<del>OE</del>	Data	Mode
Н	X	X	High Z	Standby (I <sub>SB</sub> , I <sub>SB1</sub> )
L	Н	Н	High Z	Output disable (I <sub>CC</sub> )
L	Н	L	D <sub>OUT</sub>	Read (I <sub>CC</sub> )
L	L	X	$D_{IN}$	Write (I <sub>CC</sub> )

Key: X = don't care, L = low, H = high.



## **Recommended operating conditions**

Parameter	Symbol	Min	Nominal	Max	Unit
Supply voltage	V <sub>CC</sub>	3.0	3.3	3.6	V
Input voltage	$V_{IH}$	2.0	_	$V_{CC} + 0.3$	V
input voltage	V <sub>IL</sub>	-0.5	_	0.8	V
Ambient operating temperature (Industrial)	$T_{A}$	-40	_	85	° C

### DC operating characteristics (over the operating range) $^{I}$

	_	AS7C31025C-10		.025C-10	
Parameter	Sym	<b>Test conditions</b>	Min	Max	Unit
Input leakage current	I <sub>LI</sub>	$V_{CC} = Max$ , $V_{IN} = GND$ to $V_{CC}$	_	5	μΑ
Output leakage current	I <sub>LO</sub>	$V_{CC} = Max, \overline{CE} = V_{IH},$ $V_{out} = GND \text{ to } V_{CC}$	_	5	μΑ
Operating power supply current	$I_{CC}$	$V_{CC} = Max$ $\overline{CE} \le V_{IL}, f = f_{Max},$ $I_{OUT} = 0 \text{ mA}$	_	150	mA
	$I_{SB}$	$V_{CC} = Max$ $\overline{CE} \ge V_{IH}, f = f_{Max}$	_	50	mA
Standby power supply current <sup>I</sup>	$I_{SB1}$	$\begin{aligned} V_{CC} &= \text{Max}, \overline{\text{CE}} \ge V_{CC} - 0.2 \text{ V}, \\ V_{IN} &\le 0.2 \text{ V or } V_{IN} \ge V_{CC} - 0.2 \text{ V}, \\ f &= 0 \end{aligned}$	_	10	mA
Output voltage	V <sub>OL</sub>	$I_{OL} = 8 \text{ mA}, V_{CC} = Min$	_	0.4	V
Output rorange	V <sub>OH</sub>	$I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min}$	2.4	_	V

# Capacitance (f = 1 MHz, $T_a = 25^{\circ}$ C, $V_{CC} = NOMINAL)^2$

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	$C_{IN}$	$A, \overline{CE}, \overline{WE}, \overline{OE}$	$V_{IN} = 3dV$	6	pF
I/O capacitance	C <sub>I/O</sub>	I/O	$V_{OUT} = 3dV$	7	pF

#### Note:

1. This parameter is guaranteed by device characterization, but is not production tested.

 $V_{IL}$  min = -2.0V for pulse width less than 5ns, once per cycle.  $V_{IH}$  min = -V<sub>CC</sub> + 2.0V for pulse width less than 5ns, once per cycle.



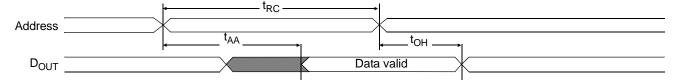
## Read cycle (over the operating range)<sup>3,9</sup>

	AS7C31025C-10				
Parameter	Symbol	Min	Max	Unit	Notes
Read cycle time	t <sub>RC</sub>	10	_	ns	
Address access time	t <sub>AA</sub>	_	10	ns	3
Chip enable (CE) access time	t <sub>ACE</sub>	_	10	ns	3
Output enable (OE) access time	t <sub>OE</sub>	_	5	ns	
Output hold from address change	t <sub>OH</sub>	4	_	ns	5
CE low to output in low Z	t <sub>CLZ</sub>	4	_	ns	4, 5
CE high to output in high Z	t <sub>CHZ</sub>	0	5	ns	4, 5
OE low to output in low Z	t <sub>OLZ</sub>	0	_	ns	4, 5
OE high to output in high Z	t <sub>OHZ</sub>	0	5	ns	4, 5
Power up time	t <sub>PU</sub>	0	_	ns	4, 5
Power down time	t <sub>PD</sub>	_	10	ns	4, 5

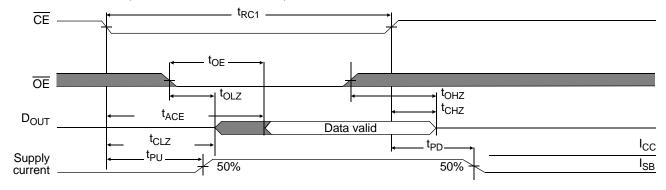
### **Key to switching waveforms**



## Read waveform 1 (address controlled)<sup>3,6,7,9</sup>



# Read waveform 2 (CE and OE controlled)<sup>3,6,8,9</sup>

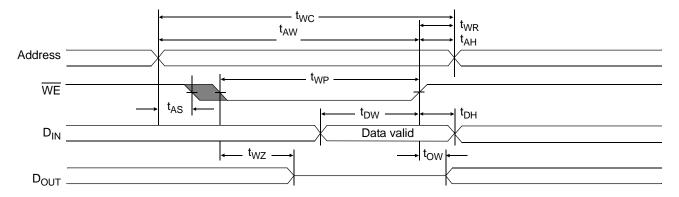




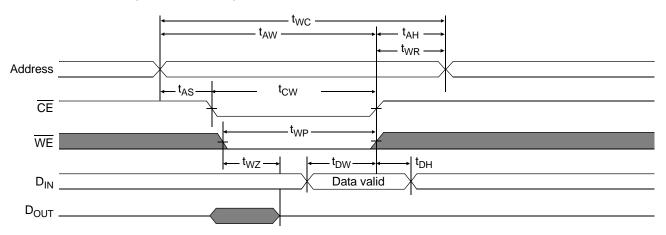
## Write cycle (over the operating range) $^{II}$

		AS7C31025C-10			
Parameter	Symbol	Min	Max	Unit	Notes
Write cycle time	$t_{WC}$	10	_	ns	
Chip enable (CE) to write end	t <sub>CW</sub>	7	_	ns	
Address setup to write end	t <sub>AW</sub>	7	_	ns	
Address setup time	t <sub>AS</sub>	0	_	ns	
Write pulse width	$t_{\mathrm{WP}}$	7	_	ns	
Write recovery time	t <sub>WR</sub>	0	_	ns	
Address hold from end of write	t <sub>AH</sub>	0	_	ns	
Data valid to write end	$t_{DW}$	5	_	ns	
Data hold time	t <sub>DH</sub>	0	_	ns	4, 5
Write enable to output in high Z	$t_{WZ}$	0	5	ns	4, 5
Output active from write end	t <sub>OW</sub>	3	_	ns	4, 5

# Write waveform 1 ( $\overline{\text{WE}}$ controlled)<sup>10,11</sup>



# Write waveform 2 ( $\overline{\text{CE}}$ controlled)<sup>10,11</sup>





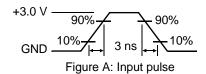
#### **AC** test conditions

- Output load: see Figure B.

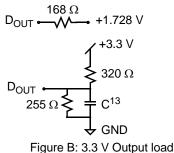
– Input pulse level: GND to 3.0 V. See Figure A.

- Input rise and fall times: 3 ns. See Figure A.

- Input and output timing reference levels: 1.5 V.



#### Thevenin equivalent:



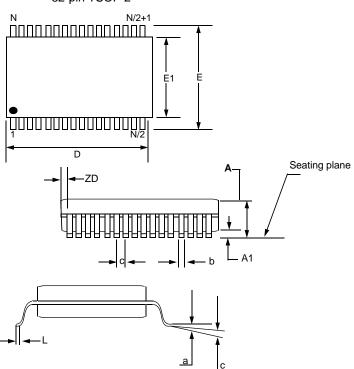
#### **Notes**

- 1 During  $V_{CC}$  power-up, a pull-up resistor to  $V_{CC}$  on  $\overline{CE}$  is required to meet  $I_{SB}$  specification.
- 2 This parameter is sampled, but not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A and B.
- $4 t_{CLZ}$  and  $t_{CHZ}$  are specified with CL = 5 pF, as in Figure B. Transition is measured  $\pm 200$  mV from steady-state voltage.
- 5 This parameter is guaranteed, but not 100% tested.
- 6 WE is high for read cycle.
- 7  $\overline{\text{CE}}$  and  $\overline{\text{OE}}$  are low for read cycle.
- 8 Address is valid prior to or coincident with  $\overline{\text{CE}}$  transition low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 N/A
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12 N/A
- 13 C = 30 pF, except all high Z and low Z parameters where C = 5 pF.



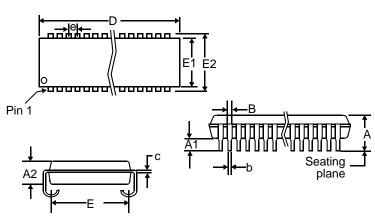
## **Package dimensions**

32-pin TSOP 2



	<b>32-pin TSOP 2 (mm)</b>			
Symbol	Min	Max		
A	_	1.20		
<b>A1</b>	0.05	0.15		
b	0.3	0.52		
C	0.12	0.21		
D	20.82	21.08		
<b>E</b> 1	10.03	10.29		
E	11.56	11.96		
e	1.27	BSC		
L	0.40	0.60		
ZD	0.95 REF.			
α	0°	5°		

32-pin SOJ 300 mil/400 mil



	32-pii 300		32-pin SOJ 400 mil		
Symbol	Min	Max	Min	Max	
A	0.128	0.145	0.132	0.146	
<b>A1</b>	0.025	-	0.025	-	
<b>A2</b>	0.095	0.105	0.105	0.115	
В	0.026	0.032	0.026	0.032	
b	0.016	0.020	0.015	0.020	
c	0.007	0.010	0.007	0.013	
D	0.820	0.830	0.820	0.830	
E	0.255	0.275	0.354	0.378	
<b>E</b> 1	0.295	0.305	0.395	0.405	
<b>E2</b>	0.330	0.340	0.435	0.445	
e	0.050	BSC	0.050	BSC	



# **Ordering Codes**

Package	Volt/Temperature	10 ns
300-mil SOJ	5V Industrial	AS7C31025C-10TJIN
400-mil SOJ	5V Industrial	AS7C31025C-10JIN
TSOP 2	5V Industrial	AS7C31025C-10TIN

## Part numbering system

AS7C	X	1025B	-XX	X	X	X	
SRAM prefix	Voltage: 3 = 3.3 V CMOS	Device number	Access time	Package: TJ = SOJ 300 mil J = SOJ 400 mil T = TSOP2	Temperature range I = industrial, -40° C to 85° C	N = Lead Free Part	





Alliance Memory, Inc. 1116 South Amphlett San Mateo, CA 94402 Tel: 650-525-3737

Fax: 650-525-0449

www.alliancememory.com

Copyright © Alliance Momory All Rights Reserved

Part Number: AS7C31025C Document Version: v. 1.0

© Copyright 2003 Alliance Memory, Inc. All rights reserved. Our three-point logo, our name and Intelliwatt are trademarks or registered trademarks of Alliance. All other brand and product names may be the trademarks of their respective companies. Alliance reserves the right to make changes to this document and its products at any time without notice. Alliance assumes no responsibility for any errors that may appear in this document. The data contained herein represents Alliance's best data and/or estimates at the time of issuance. Alliance reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general descriptive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warrantee to any user or customer. Alliance does not assume any responsibility or liability arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of Alliance products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as express agreed to in Alliance's Terms and Conditions of Sale (which are available from Alliance). All sales of Alliance products are made exclusively according to Alliance's Terms and Conditions of Sale. The purchase of products from Alliance does not convey a license under any patent rights, copyrights; mask works rights, trademarks, or any other intellectual property rights of Alliance or third parties. Alliance does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of Alliance products in such life-supporting systems implies that

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SRAM category:

Click to view products by Alliance Memory manufacturer:

Other Similar products are found below:

5962-8855206XA CY6116A-35DMB CY7C128A-45DMB CY7C1461KV33-133AXI CY7C199-45LMB GS8161Z36DD-200I GS88237CB-200I R1QDA7236ABB-20IB0 RMLV0408EGSB-4S2#AA0 IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6T4008C1B-GB70 CY7C1353S-100AXC AS6C8016-55BIN AS7C164A-15PCN 515712X IS62WV51216EBLL-45BLI IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI 47L16-E/SN IS66WVE4M16EALL-70BLI IS62WV6416DBLL-45BLI IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KV33-100BZXI CY7C1373KV33-100AXC CY7C1381KVE33-133AXI CY7C4042KV13-933FCXC 8602501XA 5962-3829425MUA 5962-8855206YA 5962-8866201XA 5962-8866201YA 5962-8866204TA 5962-8866206MA 5962-8866207NA 5962-8866208UA 5962-8872502XA 5962-8959836MZA 5962-8959841MZA 5962-9062007MXA 5962-9161705MXA N08L63W2AB7I 7130LA100PDG M38510/28902BVA 5962-8971203XA 5962-8971202ZA 5962-8872501LA 5962-8866207UA